What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	16MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, Voltage Detect, WDT
Number of I/O	41
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21208kfp-u1

1.2 Performance Overview

Table 1.1 outlines the Functions and Specifications for R8C/20 Group and Table 1.2 outlines the Functions and Specifications for R8C/21 Group.

Table 1.1 Functions and Specifications for R8C/20 Group

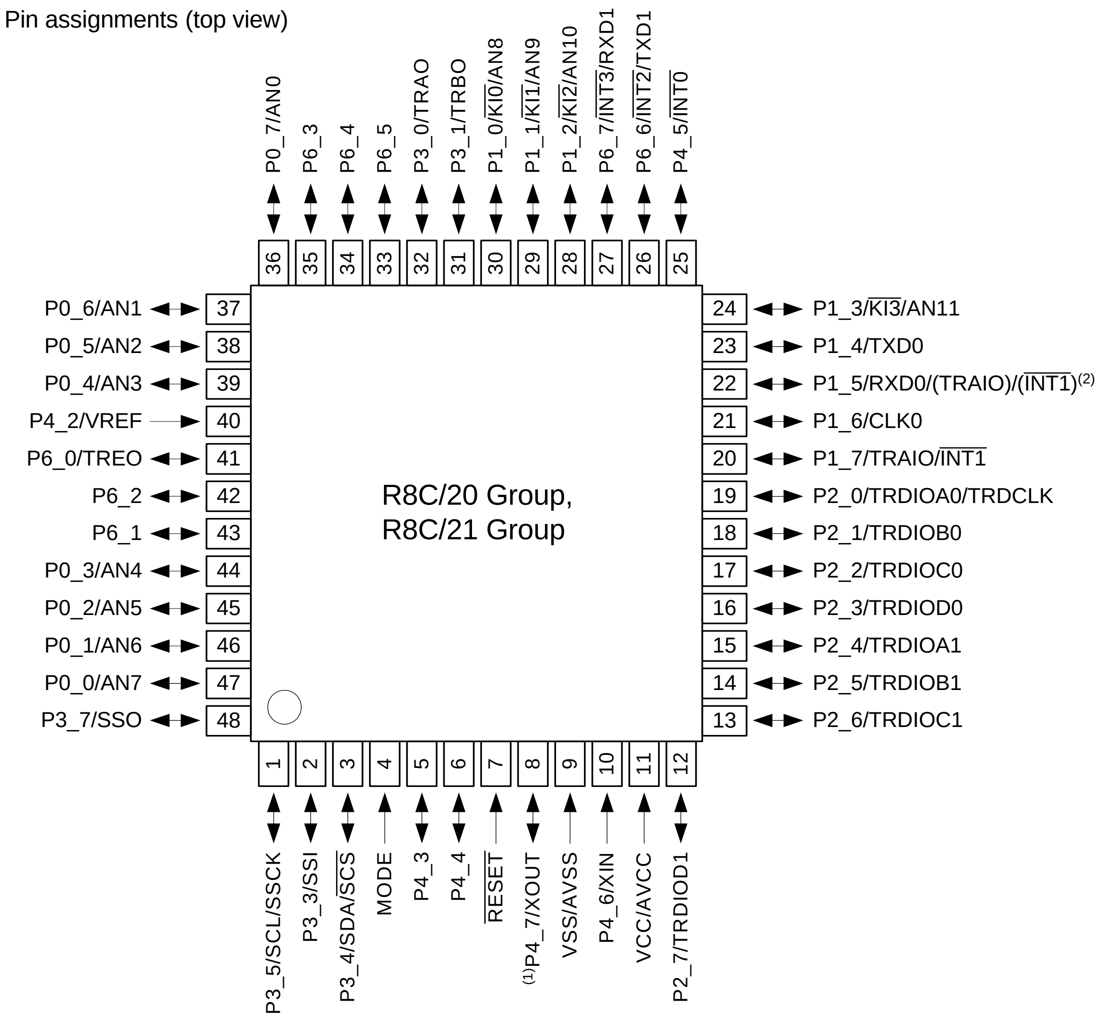
Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.3 Product Information for R8C/20 Group**
Peripheral Function	Ports	I/O ports: 41 pins, Input port: 3 pins
	Timers	Timer RA: 8 bits x 1 channel, Timer RB: 8 bits x 1 channel (Each timer equipped with 8-bit prescaler) Timer RD: 16 bits x 2 channel (Circuits of input capture and output compare) Timer RE: With compare match function
	Serial interface	1 channel (UART0) Clock synchronous I/O, UART 1 channel (UART1) UART
	Clock synchronous serial interface	1 channel I^2C bus interface(2), Clock synchronous serial I/O with chip select
	LIN module	Hardware LIN: 1 channel (timer RA, UART0)
	A/D converter	10-bit A/D converter: 1 circuit, 12 channels
	Watchdog timer	15 bits x 1 channel (with prescaler) Reset start selectable
	Interrupt	Internal: 11 sources, External: 5 sources, Software: 4 sources, Priority level: 7 levels
	Clock generation circuits	2 circuits XIN clock generation circuit (with on-chip feedback resistor) On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function.
	Oscillation stop detection function	Stop detection of XIN clock oscillation
	Voltage detection circuit	On-chip
	Power-on reset circuit include	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz)(J version) VCC = 3.0 to 5.5 V (f(XIN) = 16 MHz)(K version) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 11.0 mA (VCC = 5 V, f(XIN) = 20 MHz, High-speed on-chip oscillator stopping) Typ. 5.3 mA (VCC = 5 V, f(XIN) = 10 MHz, High-speed on-chip oscillator stopping)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	100 times
Operating Ambient Temperature		-40 to 85°C
		-40 to 125°C (option(1))
Package		48-pin mold-plastic LQFP

NOTES:

1. When using options, be sure to inquire about the specification.
2. I^2C bus is a registered trademark of Koninklijke Philips Electronics N.V.

1.5 Pin Assignments

Figure 1.4 shows Pin Assignments (Top View).



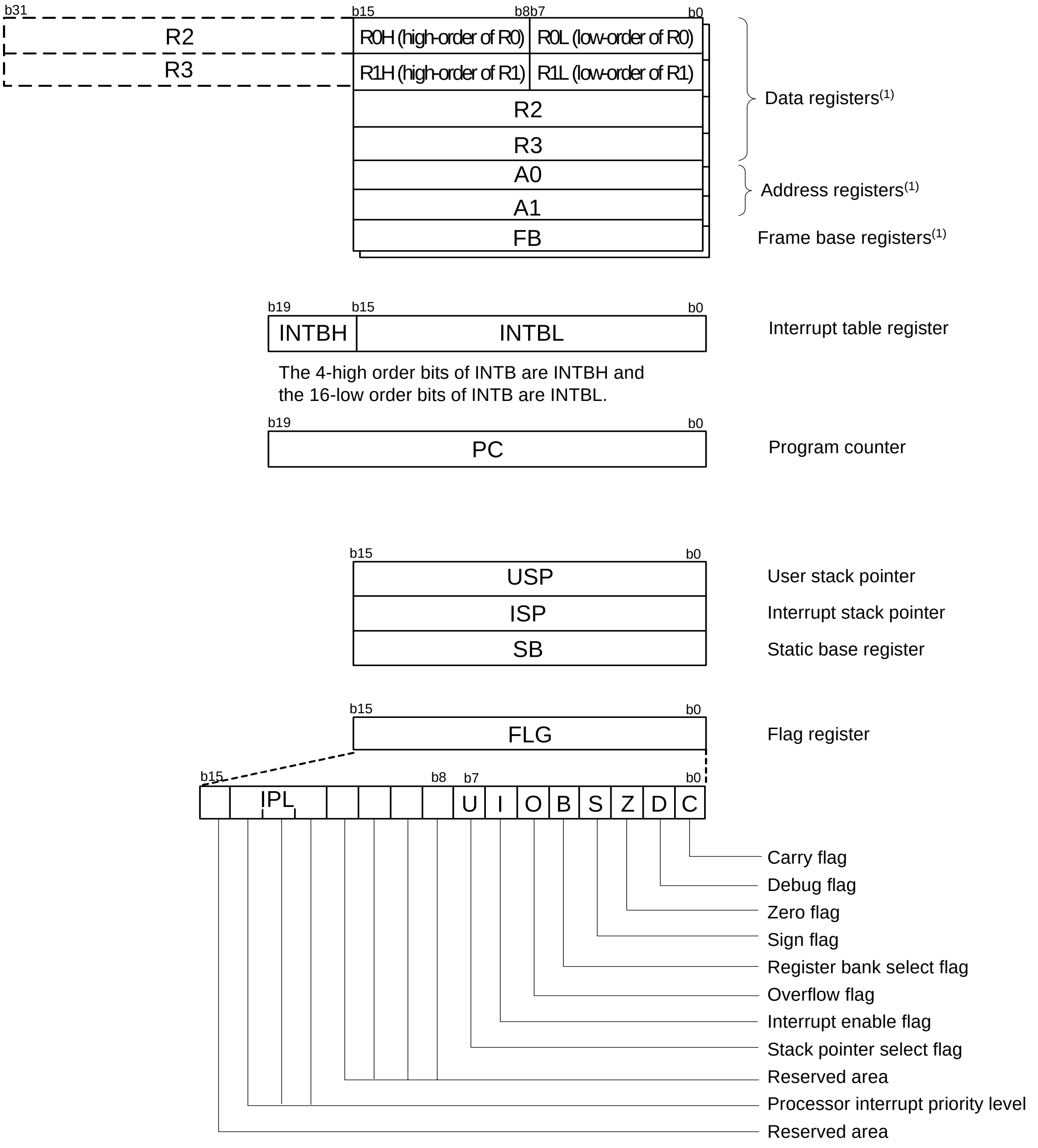
Package: PLQP0048KB-A
0.5 mm pin pitch, 7 mm square body

NOTES:
1. P4_7 is an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.4 Pin Assignments (Top View)

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. Of these, R0, R1, R2, R3, A0, A1, and FB comprise a register bank. Two sets of register banks are provided.



NOTE:
1. A register bank comprises these registers. Two sets of register banks are provided.

Figure 2.1 CPU Registers

2.8.7 Interrupt Enable Flag (I)

The I flag enables a maskable interrupt.
An interrupt is disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers. 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL, 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has greater priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/20 Group

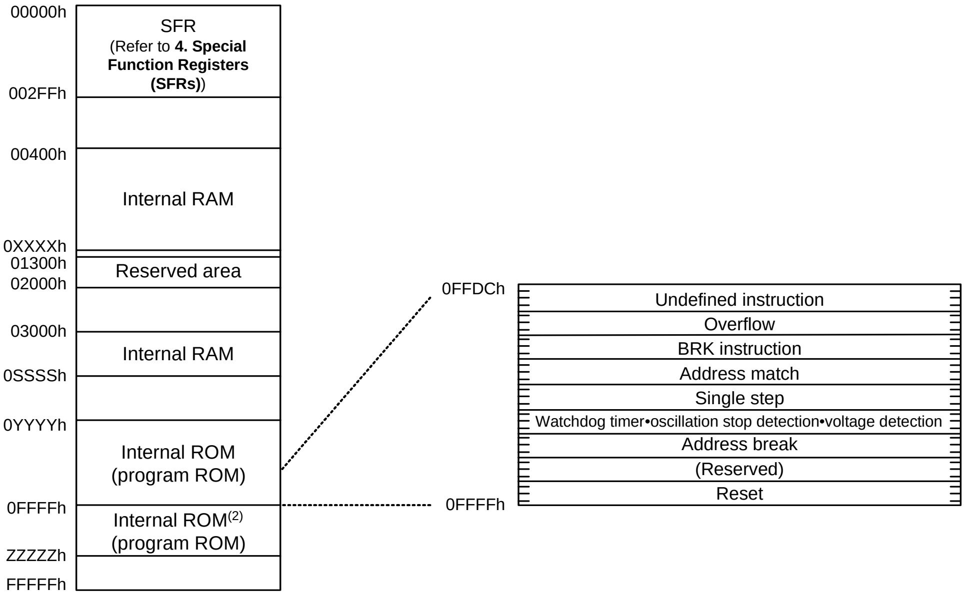
Figure 3.1 shows a Memory Map of R8C/20 Group. The R8C/20 Group has 1 Mbyte of address space from address 00000h to FFFFFh.

The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM is allocated addresses 04000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFR) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future user and cannot be accessed by users.



NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **23. Notes on Emulator Debugger** of Hardware Manual.

Part Number	Internal ROM			Internal RAM		
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0SSSSh
R5F21206JFP, R5F21206KFP	32 Kbytes	08000h	-	2 Kbytes	00BFFh	-
R5F21207JFP, R5F21207KFP	48 Kbytes	04000h	-	2.5 Kbytes	00DFFh	-
R5F21208JFP, R5F21208KFP	64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	-
R5F2120AJFP, R5F2120AKFP	96 Kbytes	04000h	1BFFFh	5 Kbytes	00FFFh	037FFh
R5F2120CJFP, R5F2120CKFP	128 Kbytes	04000h	23FFFh	6 Kbytes	00FFFh	03BFFh

Figure 3.1 Memory Map of R8C/20 Group

3.2 R8C/21 Group

Figure 3.2 shows a Memory Map of R8C/21 Group. The R8C/21 Group has 1 Mbyte of address space from address 00000h to FFFFFh.

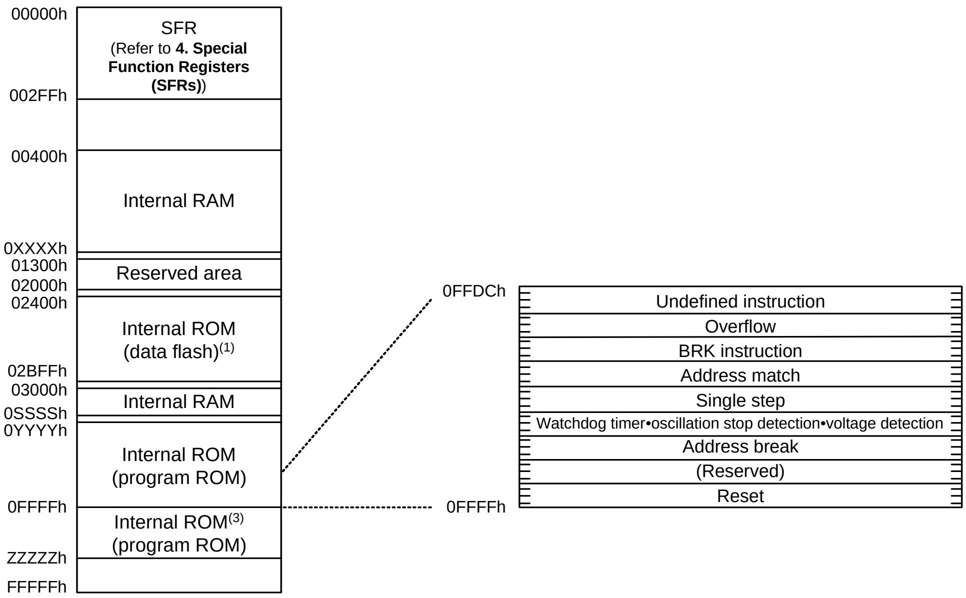
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM is allocated addresses 04000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFR) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated them. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.
3. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **23. Notes on Emulator Debugger** of Hardware Manual.

Part Number	Internal ROM			Internal RAM		
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0SSSSh
R5F21216JFP, R5F21216KFP	32 Kbytes	08000h	-	2 Kbytes	00BFFh	-
R5F21217JFP, R5F21217KFP	48 Kbytes	04000h	-	2.5 Kbytes	00DFFh	-
R5F21218JFP, R5F21218KFP	64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	-
R5F2121AJFP, R5F2121AKFP	96 Kbytes	04000h	1BFFFh	5 Kbytes	00FFFh	037FFh
R5F2121CJFP, R5F2121CKFP	128 Kbytes	04000h	23FFFh	6 Kbytes	00FFFh	03BFFh

Figure 3.2 Memory Map of R8C/21 Group

4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function.
Table 4.1 to Table 4.6 list the SFR Information.

Table 4.1 SFR Information (1)(1)

Address	Register	Symbol	After reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h
0006h	System Clock Control Register 0	CM0	01101000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h			
0009h			
000Ah	Protect Register	PRCR	00h
000Bh			
000Ch	Oscillation Stop Detection Register	OCD	00000100b
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDC	00X11111b
0010h	Address Match Interrupt Register 0	RMAD0	00h
0011h			00h
0012h			00h
0013h	Address Match Interrupt Enable Register	AIER	00h
0014h	Address Match Interrupt Register 1	RMAD1	00h
0015h			00h
0016h			00h
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protect Mode Register	CSPR	00h 10000000b(8)
001Dh			
001Eh			
001Fh			
0020h			
0021h			
0022h			
0023h	High-Speed On-Chip Oscillator Control Register 0	FRA0	00h
0024h	High-Speed On-Chip Oscillator Control Register 1	FRA1	When shipping
0025h	High-Speed On-Chip Oscillator Control Register 2	FRA2	00h
0026h			
0030h			
0031h	Voltage Detection Register 1(2)	VCA1	00001000b
0032h	Voltage Detection Register 2(6)	VCA2	00h(3) 01000000b(4)
0033h			
0034h			
0035h			
0036h	Voltage Monitor 1 Circuit Control Register(7)	VW1C	0000X000b(3) 0100X001b(4)
0037h	Voltage Monitor 2 Circuit Control Register(5)	VW2C	00h
0038h			
0039h			
003Fh			

X: Undefined
NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. Software reset, watchdog timer reset, and voltage monitor 2 reset do not affect this register.
3. The LVD0ON bit in the OFS register is set to 1.
4. Power-on reset, voltage monitor 1 reset or the LVD0ON bit in the OFS register is set to 0.
5. Software reset, watchdog timer reset, and voltage monitor 2 reset do not affect b2 and b3.
6. Software reset, watchdog timer reset, and voltage monitor 2 reset do not affect b7.
7. Software reset, the watchdog timer rest, and the voltage monitor 2 reset do not affect other than the b0 and b6.
8. The CSPROINI bit in the OFS register is 0.

Table 4.4 SFR Information (4)[1]

Address	Register	Symbol	After reset
00C0h	A/D Register	AD	XXh
00C1h			XXh
00C2h			
00C3h			
00C4h			
00C5h			
00C6h			
00C7h			
00C8h			
00C9h			
00CAh			
00CBh			
00CCh			
00CDh			
00CEh			
00CFh			
00D0h			
00D1h			
00D2h			
00D3h			
00D4h	A/D Control Register 2	ADCON2	00h
00D5h			
00D6h	A/D Control Register 0	ADCON0	00h
00D7h	A/D Control Register 1	ADCON1	00h
00D8h			
00D9h			
00DAh			
00DBh			
00DCh			
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	XXh
00E1h	Port P1 Register	P1	XXh
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h	Port P2 Register	P2	XXh
00E5h	Port P3 Register	P3	XXh
00E6h	Port P2 Direction Register	PD2	00h
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h			
00EAh	Port P4 Direction Register	PD4	00h
00EBh			
00ECh	Port P6 Register	P6	XXh
00EDh			
00EEh	Port P6 Direction Register	PD6	00h
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h			
00F5h	UART1 Function Select Register	U1SR	XXh
00F6h			
00F7h			
00F8h	Port Mode Register	PMR	00h
00F9h	External Input Enable Register	INTEN	00h
00FAh	INT Input Filter Select Register	INTF	00h
00FBh	Key Input Enable Register	KIEN	00h
00FCh	Pull-Up Control Register 0	PUR0	00h
00FDh	Pull-Up Control Register 1	PUR1	XX00XX00b
00FEh			
00FFh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated value	Unit
V_{CC}/AV_{CC}	Supply voltage		-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC}+0.3	V
V_O	Output voltage		-0.3 to V_{CC}+0.3	V
P_d	Power dissipation	-40°C ≤ Topr ≤ 85°C	300	mW
		85°C < Topr ≤ 125°C	125	mW
T_{opr}	Operating ambient temperature		-40 to 85 (J version) / -40 to 125 (K version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.7	–	5.5	V
V_{SS}/AV_{CC}	Supply voltage			–	0	–	V
V_{IH}	Input "H" voltage			0.8V_{CC}	–	V_{CC}	V
V_{IL}	Input "L" voltage			0	–	0.2V_{CC}	V
$I_{OH(sum)}$	Peak sum output "H" current	Sum of all Pins $I_{OH\ (peak)}$		–	–	-60	mA
$I_{OH(peak)}$	Peak output "H" current			–	–	-10	mA
$I_{OH(avg)}$	Average output "H" current			–	–	-5	mA
$I_{OL(sum)}$	Peak sum output "L" currents	Sum of all Pins $I_{OL\ (peak)}$		–	–	60	mA
$I_{OL(peak)}$	Peak output "L" currents			–	–	10	mA
$I_{OL(avg)}$	Average output "L" current			–	–	5	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 85°C	0	–	20	MHz
			3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 125°C	0	–	16	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
–	System clock	OCD2 = 0 When XIN clock is selected.	3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 85°C	0	–	20	MHz
			3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 125°C	0	–	16	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
		OCD2 = 1 When on-chip oscillator clock is selected.	FRA01 = 0 When low-speed on-chip oscillator clock is selected.	–	125	–	kHz
			FRA01 = 1 When high-speed on-chip oscillator clock is selected. 3.0 V ≤ V_{CC} ≤ 5.5 V -40°C ≤ Topr ≤ 85°C	–	–	20	MHz
			FRA01 = 1 When high-speed on-chip oscillator clock is selected.	–	–	10	MHz

NOTES:

1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance[2]	R8C/20 Group	100[3]	–	–	times
		R8C/21 Group	1,000[3]	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until erase suspend		–	–	97 + CPU clock × 6 cycle	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time[7]	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times.
   For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure endurance can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data Flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (Program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (Program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (Program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (Program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until erase suspend		–	–	97 + CPU clock × 6 cycle	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-40	–	85(8)	°C
–	Data hold time(9)	Ambient temperature = 55°C	20	–	–	year

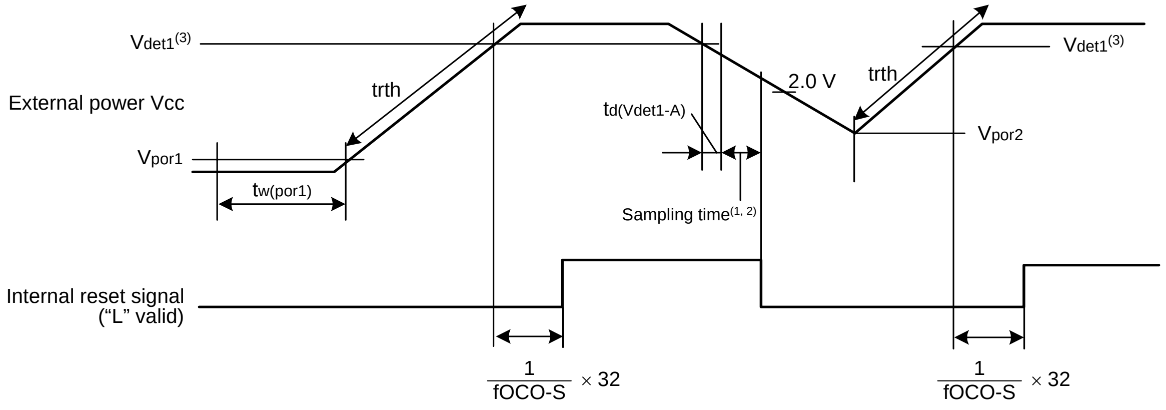
NOTES:

1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times.
   For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. MInimum endurance to guarantee all electrical characteristics after program and erase (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times are the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure endurance can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. 125°C for K version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.8 Power-on Reset Circuit, Voltage Monitor 1 Reset Circuit Electrical Characteristics(3)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage(4)		–	–	0.1	V
V_{por2}	Power-on reset or voltage monitor 1 valid voltage		0	–	Vdet1	V
trth	External power V_{CC} rise gradient	$V_{CC} \leq 3.6$ V	20(2)	–	–	mV/msec
		$V_{CC} > 3.6$ V	20(2)	–	2,000	mV/msec

NOTES:
1. Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version), unless otherwise specified.
2. This condition (the minimum value of external power V_{CC} rise gradient) does not apply if $V_{por2} \geq 1.0$ V.
3. To use the power-on reset function, enable voltage monitor 1 reset by setting the LVD1ON bit in the OFS register to 0, the VW1C0 and VW1C6 bits in the VW1C register to 1 respectively, and the VCA26 bit in the VCA2 register to 1.
4. $t_{w(por1)}$ indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain tw(por1) for 30s or more if -20°C ≤ Topr ≤ 125°C, maintain $t_{w(por1)}$ for 3,000s or more if -40°C ≤ Topr < -20°C.



NOTES:
1. When using the voltage monitor 1 digital filter, ensure VCC is 2.0 V or higher during the sampling time.
2. The sampling clock can be selected. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.
3. V_{det1} indicates the voltage detection level of the voltage detection 1 circuit. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.

Figure 5.3 Power-on Reset Circuit Electrical Characteristics

Table 5.9 High-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	VCC = 4.75 V to 5.25 V, 0°C ≤ Topr ≤ 60°C(2)	39.2	40	40.8	MHz
		VCC = 3.0 V to 5.25 V, -20°C ≤ Topr ≤ 85°C(2)	38.8	40	41.2	MHz
		VCC = 3.0 V to 5.5 V, -40°C ≤ Topr ≤ 85°C(2)	38.4	40	41.6	MHz
		VCC = 3.0 V to 5.5 V, -40°C ≤ Topr ≤ 125°C(2)	38.0	40	42.0	MHz
		VCC = 2.7 V to 5.5 V, -40°C ≤ Topr ≤ 125°C(2)	37.6	40	42.4	MHz
–	The value of the FRA1 register when the reset is deasserted		08h	40	F7h	–
–	High-speed on-chip oscillator adjustment range	Adjust the FRA1 register to -1 bit (the value when the reset is deasserted)	–	+ 0.3	–	MHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption when high-speed on-chip oscillator oscillating	VCC = 5.0 V, Topr = 25°C	–	600	–	µA

NOTES:

1. VCC = 2.7 V to 5.5 V, Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version), unless otherwise specified.
2. The standard value shows when the reset is deasserted for the FRA1 register.

Table 5.10 Low-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		40	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption when low-speed on-chip oscillator oscillating	VCC = 5.0 V, Topr = 25°C	–	15	–	µA

NOTE:

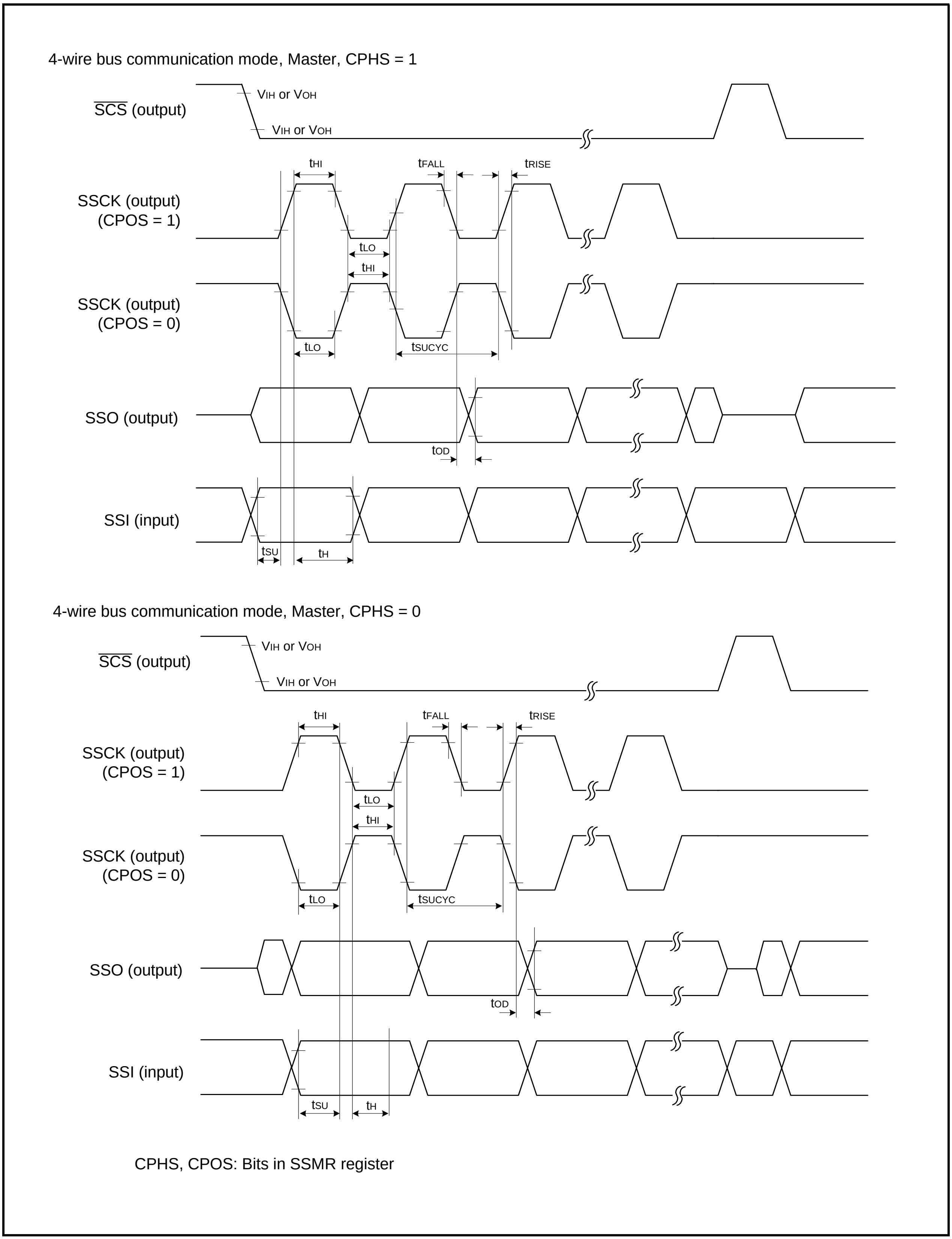
1. VCC = 2.7 V to 5.5 V, Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version), unless otherwise specified.

Table 5.11 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:

1. The measurement condition is VCC = 2.7 to 5.5 V and Topr = -40°C to 85°C (J version) / -40°C to 125°C (K version), unless otherwise specified.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until CPU clock supply starts since the interrupt is acknowledged to exit stop mode.


4-wire bus communication mode, Master, CPHS = 1

4-wire bus communication mode, Master, CPHS = 0

CPHS, CPOS: Bits in SSMR register

Figure 5.4 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

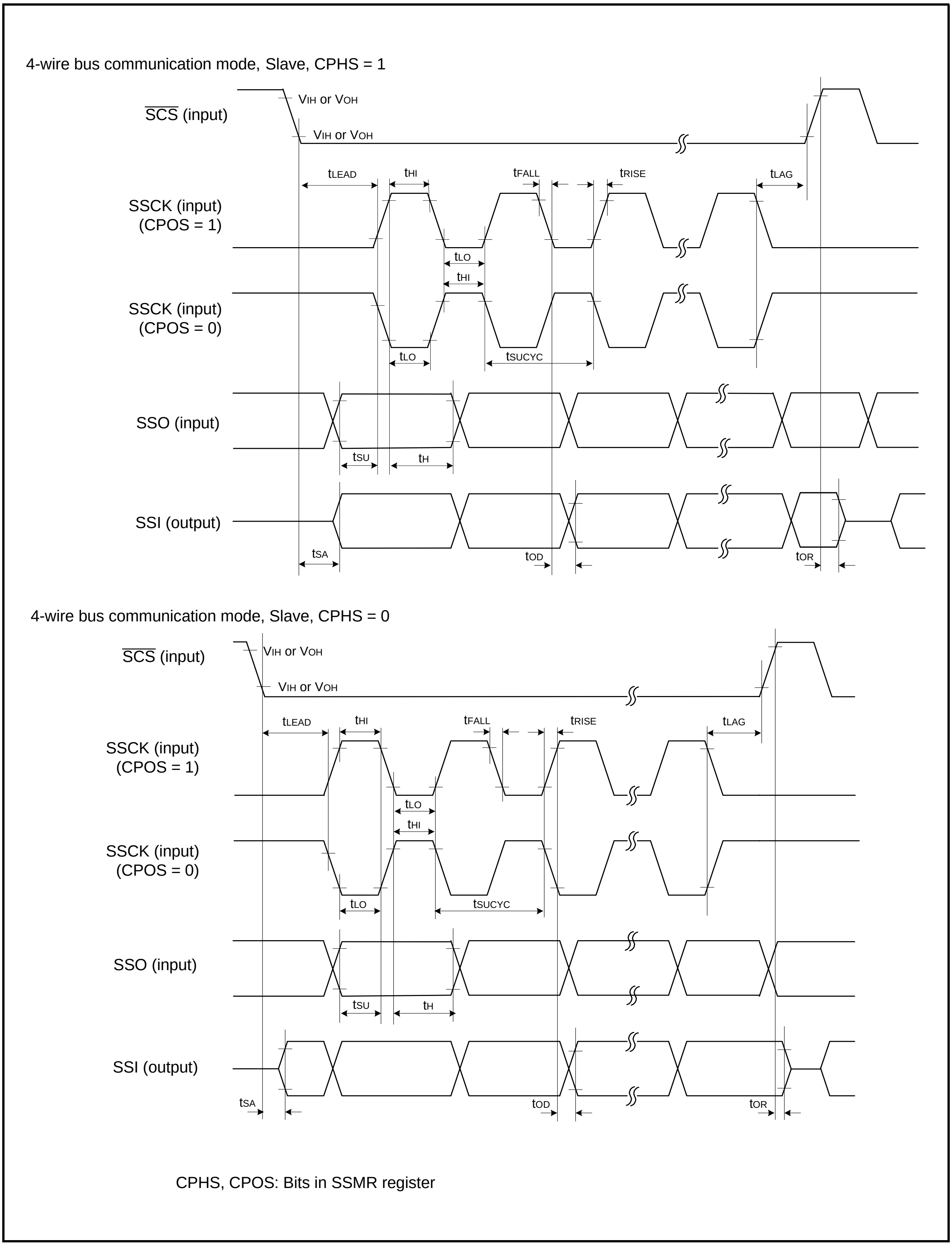


Figure 5.5 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

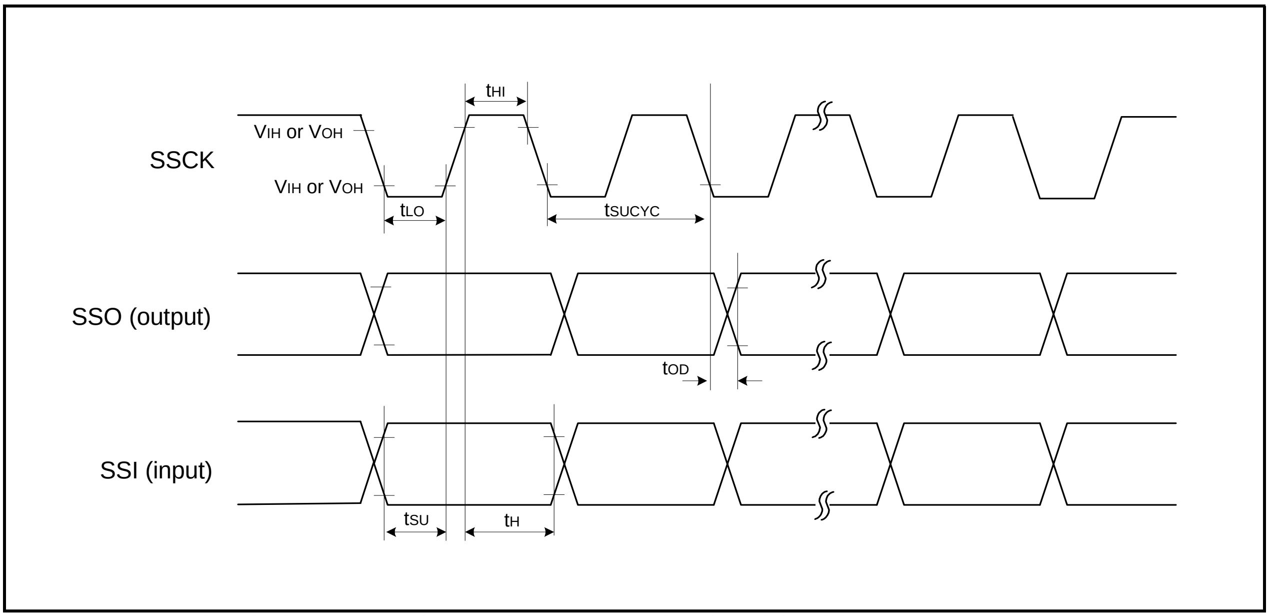


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.14 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” Voltage	Except XOUT	I_{OH} = -5 mA		V_{CC} – 2.0	–	V_{CC}	V
			I_{OH} = -200 μA		V_{CC} – 0.3	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 μA	V_{CC} – 2.0	–	V_{CC}	V
V_{OL}	Output “L” Voltage	Except XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT2}}$, $\overline{\text{INT3}}$, $\overline{\text{KI0}}$, $\overline{\text{KI1}}$, $\overline{\text{KI2}}$, $\overline{\text{KI3}}$, TRAIO, RXD0, RXD1, CLK0, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{\text{RESET}}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5 V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5 V		–	–	-5.0	μA
R_{PULLUP}	Pull-Up Resistance		VI = 0 V, V_{CC} = 5 V		30	50	167	kΩ
R_{fXIN}	Feedback Resistance	XIN			–	1.0	–	MΩ
V_{RAM}	RAM Hold Voltage		During stop mode		2.0	–	–	V

NOTE:

1. V_{CC} = 4.2 to 5.5 V at Topr = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.15 Electrical Characteristics (2) [VCC = 5 V]
(Topr = -40 to 85°C (J version) / -40 to 125°C (K version), Unless Otherwise Specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 3.3 to 5.5 V) In single-chip mode, the output pins are open and other pins are VSS	High-clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	11.0	22.0	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	8.8	17.6	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5.8	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5.0	–	mA
			XIN = 16MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.8	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.8	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.8	11.6	mA
			XIN clock off High-speed on-chip oscillator on fOCO= 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	143	286	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA20 = 0 VCA26 = VCA27 = 0	–	53	106	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA20 = 0 VCA26 = VCA27 = 0	–	38	76	µA
		Stop mode Topr = 25°C	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA26 = VCA27 = 0	–	0.8	3.0	µA
		Stop mode Topr = 85°C	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA26 = VCA27 = 0	–	1.2	–	µA
		Stop mode Topr = 125°C	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA26 = VCA27 = 0	–	4.0	–	µA

Rev.	Date	Description	
		Page	Summary
0.20	Sep 29, 2005	20	Table 4.6 SFR Information (6) revised - 0145h: POCR0 → TRDPOCR0 - 0146h, 0147h: TRDCNT0 → TRD0 - 0148h, 0149h: GRA0 → TRDGRA0 - 014Ah, 014Bh: GRB0 → TRDGRB0 - 014Ch, 014Dh: GRC0 → TRDGRC0 - 014Eh, 014Fh: GRD0 → TRDGRD0 - 0155h: POCR1 -> TRDPOCR1 - 0156h, 0157h: TRDCNT1 → TRD1 - 0158h, 0159h: GRA1 → TRDGRA1 - 015Ah, 015Bh: GRB1 → TRDGRB1 - 015Ch, 015Dh: GRC1 → TRDGRC1 - 015Eh, 015Fh: GRD1 → TRDGRD1
		22	5. Electrical Characteristics added
1.00	Nov 15, 2006	All pages	“Preliminary” and “Under development” deleted
		2	Table 1.1 Functions and Specifications for R8C/20 Group revised. NOTE1 deleted.
		3	Table 1.2 Functions and Specifications for R8C/21 Group revised. NOTE1 deleted.
		5	Table 1.3 Product Information for R8C/20 Group; “R5F2120AJFP (D)”, “R5F2120CJFP (D)”, “R5F2120AKFP (D)”, “R5F2120CKFP (D)”, and NOTE added. Figure 1.2 Type Number, Memory Size, and Package of R8C/20 Group; “A: 96 KB” and “C: 128 KB” added.
		6	Table 1.4 Product Information for R8C/21 Group; “R5F2121AJFP (D)”, “R5F2121CJFP (D)”, “R5F2121AKFP (D)”, “R5F2121CKFP (D)”, and NOTE added. Figure 1.3 Type Number, Memory Size, and Package of R8C/21 Group; “A: 96 KB” and “C: 128 KB” added.
		13	Figure 3.1 Memory Map of R8C/20 Group revised.
		14	Figure 3.2 Memory Map of R8C/21 Group revised.
		15	Table 4.1 SFR Information (1)(1); NOTE8; “The CSPROINI bit in the OFS register is set to 0.” → “The CSPROINI bit in the OFS register is 0.” revised.
		21	Table 5.1 Absolute Maximum Ratings; Power dissipation revised. Table 5.2 Recommended Operating Conditions; System clock revised.
		26	Table 5.8 Voltage Monitor 1 Reset Circuit Electrical Characteristics → Table 5.8 Power-on Reset Circuit, Voltage Monitor 1 Reset Circuit Electrical Characteristics(1) replaced. Table 5.8 revised. NOTE3 added. Table 5.9 Power-on Reset Circuit Electrical Characteristics deleted. Figure 5.3 Power-on Reset Circuit Electrical Characteristics revised.
		27	Table 5.10 High-Speed On-Chip Oscillator Circuit Electrical Characteristics → Table 5.9 High-Speed On-Chip Oscillator Circuit Electrical Characteristics revised.

REVISION HISTORY	R8C/20 Group, R8C/21 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Nov 15, 2006	33	Table 5.15 Electrical Characteristics (1) [VCC = 5 V] → Table 5.14 Electrical Characteristics (1) [VCC = 5 V] revised. RAM Hold Voltage, Min.; “1.8” → “2.0” corrected.
		34	Table 5.16 Electrical Characteristics (2) [Vcc = 5 V] → Table 5.15 Electrical Characteristics (2) [Vcc = 5 V] revised. Wait mode revised.
		37	Table 5.21 Electrical Characteristics (3) [VCC = 3 V → Table 5.20 Electrical Characteristics (3) [VCC = 3 V] revised. RAM hold voltage, Min.;“1.8” → “2.0” corrected.
		38	Table 5.22 Electrical Characteristics (4) [Vcc = 3 V] → Table 5.21 Electrical Characteristics (4) [Vcc = 3 V] revised. Wait mode revised.
2.00	Aug 27, 2008	–	“RENESAS TECHNICAL UPDATE” reflected: TN-16C-A172A/E
		5, 6	Table 1.3, Table 1.4 revised Figure 1.2, Figure 1.3; ROM number “XXX” added
		13, 14	Figure 3.1, Figure 3.2; “Expanding area” deleted
		21	Table 5.2; NOTE2 revised
		23	Table 5.4; NOTE2 and NOTE4 revised
		24	Table 5.5; NOTE2 and NOTE5 revised
		25	Table 5.6; “td(Vdet1-A)” added, NOTE5 added Table 5.7; “td(Vdet2-A)” and NOTE2 revised, NOTE5 added
		26	Table 5.8; “trth” and NOTE2 revised Figure 5.3 revised